

Remarks

In response to the species election requirement contained in the Office Action Applicant elects Species 7: Figures 7A-7I. Claims 34-35, 38-41, 43 and 49-51 read on the elected species. This is the same election as contained in the Amendment dated November 19, 2001, and the same species election requirement of the Office Action dated 10/18/01.

A reading of the claims on the drawings and specification is as follow.

34. A method for fabricating an interconnect (10-
Figure 1, page 9, lines 6-30 of the specification) for engaging a bumped contact (16-**Figure 2C page 9, lines 6-30 of the specification**) on a semiconductor component (18-
Figure 2C page 9, lines 6-30 of the specification) comprising:

providing a substrate (14B-**Figure 7A, page 18, line 33 to page 19, line 3 of the specification**);

forming a plurality of leads (22B-**Figure 7C, page 19, lines 10-14 of the specification**) on the substrate configured to electrically engage and support the bumped contact (**Figure 3B, page 4, lines 18-21 of the specification**);

forming a recess (20B-**Figure 7F, page 21, lines 10-14 of the specification**) in the substrate such that the leads cantilever over the recess and are configured for movement within the recess during electrical engagement of the bumped contact (**Figure 3B, page 4, lines 18-21 of the specification**); and

forming an outer layer (46B-**Figure 7B and 3D, page 19, lines 4-9 of the specification**) on each lead configured to provide a non-bonding surface for the bumped contact (**page 13, line 27, to page 14, line 2 of the specification**).

35. The method of claim 34 wherein the outer layer (46B-**Figure 7B and 3D, page 19, lines 4-9 of the specification**) comprises a material selected from the group consisting of Ti, TiSi₂, Al and a conductive polymer (**page 13, line 30 to page 14, line 2 of the specification**).

38. The method of claim 34 further comprising forming at least one blade (28B-**Figure 7B, page 19, lines 4-5 of the specification**) on each lead configured to penetrate the bumped contact (**page 12, lines 33-34 of the specification**).

39. A method for fabricating an interconnect (10-**Figure 1, page 9, lines 6-30 of the specification**) for engaging a bumped contact (16-**Figure 2C page 9, lines 6-30 of the specification**) on a semiconductor component (18-**Figure 2C page 9, lines 6-30 of the specification**) comprising:

providing a substrate (14B-**Figure 7A, page 18, line 33 to page 19, line 3 of the specification**);

forming a metal layer (leads 22B-**Figure 7C, page 19, lines 10-14 of the specification**) on the substrate;

forming a plurality of blades (28B-**Figure 7B, page 19, lines 4-5 of the specification**) in the metal layer configured to penetrate the bumped contact (**page 12, lines 33-34 of the specification**);

forming an outer layer (46B-**Figure 7B and 3D, page 19, lines 4-9 of the specification**) on the metal layer configured to provide a non-bonding surface for the bumped contact (**page 13, line 27, to page 14, line 2 of the specification**);

forming a plurality of leads **Figure 7C, page 19, lines 10-14 of the specification**) in the metal layer configured to electrically engage and support the bumped contact

(Figure 3B, page 4, lines 18-21 of the specification), each lead including at least one blade; and

forming a recess (20B-Figure 7F, page 21, lines 10-14 of the specification) in the substrate such that the leads are cantilevered over the recess and are configured to move within the recess during electrical engagement of the bumped contact (Figure 3B, page 4, lines 18-21 of the specification).

40. The method of claim 39 wherein the outer layer comprises a conductive polymer **(page 14, lines 1-2 of the specification)**.

41. The method of claim 39 wherein the outer layer comprises a material selected from the group consisting of a carbon film and a metal filled silicone **(page 14, lines 1-2 of the specification)**.

43. The method of claim 39 further comprising forming a connecting segment **(40B-Figure 7F, page 19, lines 11-14 of the specification)** on the substrate electrically connecting the leads, a conductive via **(42B-Figure 7E, page 19, line 15 to page 20, line 31 of the specification)** in the substrate in electrical communication with the connecting segment and a contact **(38B-Figure 7F, page 20, line 32 to page 21, line 9 of the specification)** on the substrate in electrical communication with the conductive via.

49. A method for fabricating an interconnect **(10-Figure 1, page 9, lines 6-30 of the specification)** for engaging a bumped contact **(16-Figure 2C page 9, lines 6-30 of the specification)** on a semiconductor component **(18-Figure 2C page 9, lines 6-30 of the specification)** comprising: providing a substrate having a surface and

an opposing surface (**14B-Figure 7A, page 18, line 33 to page 19, line 3 of the specification**);

forming a plurality of interconnect contacts (**14B-Figure 7G, page 18, line 2 to page 21 line 20 in the specification**) on the substrate configured to electrically engage the bumped contacts (**page 9, line 26**), each interconnect contact comprising a recess (**20B-Figure 7F, page 21, lines 10-14 of the specification**) in the surface and a plurality of leads cantilevered over the recess configured to support a bumped contact for movement in the recess (**Figure 3B, page 4, lines 18-21 of the specification**); and

forming an outer layer (**46B-Figure 7B and 3D, page 19, lines 4-9 of the specification**) on each lead configured to provide non-bonding surfaces for the bumped contacts (**page 13, line 27, to page 14, line 2 of the specification**).

50. The method of claim 49 wherein the outer layer comprises a conductive polymer (**page 14, lines 1-2 of the specification**).

51. The method of claim 49 further comprising forming at least one blade (**28B-Figure 7B, page 19, lines 4-5 of the specification**) on each lead configured to penetrate a bumped contact (**page 12, lines 33-34 of the specification**).

Conclusion

The specification is also being amended to correct informalities on pages 13 and 19 (46A changed to 46B). Favorable consideration and allowance of claims 34-35, 38-41, 43 and 49-51 is respectfully requested. An Information Disclosure Statement is being filed concurrently with this Amendment. Should any issues arise that will advance this case to allowance, the Examiner is asked to contact the undersigned by telephone.

DATED this 15th day of August, 2003.

Respectfully submitted:



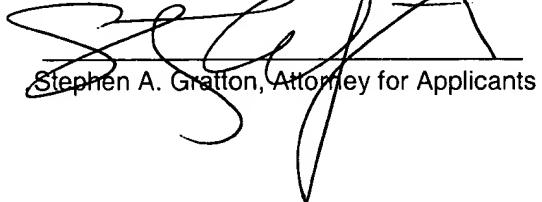
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August 15, 2003
Date of Signature



Stephen A. Gratton, Attorney for Applicants